

GigaDevice Semiconductor Inc.

GD30WS8662x Linear Charger for Wearable Application

Datasheet



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Features

- Extreme low quiescent current, 6.5uA in discharge mode
- 200nA shipping mode
- Charging features
 - Charging up to 456mA, programmable via I²C
 - Full charge cycle: pre-charge, constant current, constant voltage, charge done and auto-recharge
 - Pre-charging current and termination current programmable via I²C
 - Support variety of battery chemistries, 3.6V~4.54V can be programmabled via I²C
 - High charge voltage accuracy +/-0.5%
- Power path management
 - Power path management allows simultaneous battery charging and system supply
 - Dynamic balance of current to charge battery and to the system
 - Over voltage protection up to 32V and over current protection @1.7A
- Protection features
 - Input Over Voltage/Current Protection
 - Short Circuit Protection
 - Over/Under temperature protection
 - Overvoltage (OV) during charge
 - Undervoltage (UV) when charge/discharge
- Additional features
 - Simple I²C compatible interface
 - LDO support 50mA
 - WLCSP-9 compact package with low external component count

2 Applications

- TWS earbuds charging case
- Headsets and hearing aids
- Low battery applications such as smart watches and fitness accessories
- Patient monitors and portable medical equipment



3 General description

The GD30WS8662x is a highly integrated Li-ion charger IC for wearable and IoT applications. The IC integrates a high accuracy linear charger of programmable charging current (up to 456mA). The device also includes power path management and high input protection functions. A low quiescent current, low noise LDO capable of delivering 50mA load current is also implemented internally.

The device integrates advanced power path management and control that allows the device to provide power to the system while charging the battery even with poor adapters. The dynamic power path management is able to automatically balance the currents delivered to the system and battery charging. A high voltage and over current protection circuit is implemented in the IC to protect it from high input voltage as high as 32V.

The GD30WS8662x device supports charge current up to 456mA and supports termination current down to 1mA. The maximum charge current is set at a default of 128mA and is programmable via I²C. The battery is charged using a standard Li-Ion charge profile with three phases: pre-charge, constant current and constant voltage regulation.

The device has several power saving modes to increase battery life whether the product is in storage or in operation.

The versatile features of GD30WS8662x allow for it to best used in wearable applications such as headsets, earbuds and hearing aids, or low battery applications such as smart watches and fitness accessories, or patient monitors and portable medical equipment.

The GD30WS8662x is available in a compact WLCSP-9 1.75mmx1.75mm package.



4 Device overview

4.1 Device information

Table 4-1 Device Information for GD30WS8662X

Part Order Code	Package	Description	
GD30WS8662DY	WLCSP-9	Linear charger for wearable applition	

4.2 Block diagram

Figure 4-1 Block Diagram for GD30WS8662x





4.3 Pinout and pin assignment



Figure 4-2 GD30WS8662x WLCSP-9 Pinouts

4.4 Pin definitions

Table 4-2. GD30WS8662x PIN Configuration

Pin Name	Pins	Pin Type	Functions description
BUS	A1	Ρ	Input power pin . Power input from BUS or other 5-V voltage source. Connect a ceramic capacitor from BUS to GND as close to IC as possible.
SYS	A2	Ρ	System power supply . Connect a ceramic capacitor from SYS to GND as close to IC as possible.
BAT	A3	Ρ	Battery pin . Connect to battery positive node. Connect a ceramic capacitor from BAT to GND as close to IC as possible.
NTC	B1	I/O	Temperature sense input . Connect a negative temperature coefficient thermistor to NTC. Program the hot and cold temperature window with a resistor divider from VCC to NTC to GND. Charging is suspended when NTC is out of the range. Pull NTC to VCC if NTC function is not used.
INT B2		I/O	Open drain interrupt output . Send charge status and fault interruption to host.
VCC	B3	I/O	Internal control power supply pin. LDO output voltage, connect a 1uF ceramic capacitor from VCC to GND.
SCL	C1	I/O	I ² C communication from/to the host controller, clock.



Pin Name	Pins	Pin Type	Functions description
SDA	C2	0	I ² C communication to the host controller, data.
GND	C3	G	Ground.

Notes:

1. Type: O = Output, I/O = Input or Output, P = Power, G = Ground.



5 Functional description

5.1 **Power supply**

The internal bias circuit of the IC is powered from the higher voltage of either BUS or BAT. When BUS or BAT rises above its respective under-voltage (UVLO) threshold, the sleep comparator, battery depletion comparator, and BATFET(Q2) driver are all active. The I²C interface is ready for communication, and all register are reset to the default value. The host can access all of the register.

5.2 Operation mode

The GD30WS8662x has three different operation modes: shipping, battery operation and BUS operation mode, as shown in Figure 5-1. The mode of operation is saved in REG04 bit[12:8].



Figure 5-1 GD30WS8662x Operation Modes.

5.3 Battery charge

The GD30WS8662x device integrates a linear charger that allows the battery to be charged with a programmable charge current up to 456mA. In addition to the charge current, other charging parameters can be also programmed through I²C such as the battery regulation voltage, pre-charge current and termination charge current. The device supports multiple battery regulation voltage regulation settings (V_{REG}) and charge current (I_{CHG}) options to support multiple battery chemistries for single-cell applications. A full one-cell linear charger state diagram as shown in Figure 5-2 is implemented in the IC.







The GD30WS8662x provide three main charging phases: Pre-charge, Constant current charge and constant voltage charge in Figure 5-3.

Phase 1 (pre-charge): The GD30WS8662x can safely pre-charge the deeply depleted battery until the battery voltage reaches the pre-charge to constant current threshold(V_{BAT_PRE}). The pre-charge current is also programmed through REG01H bit[3:0]. The pre-charge current is equal to 20% of the lcc. The pre-charge current is also programmed



through REG01H bit[3:0]. If V_{BAT_PRE} is not reached before the pre-charge timer (1hr) expires, the charge cycle stop, and a corresponding timeout fault signal is asserted.

Phase 2 (constant-current charge): When the battery voltage exceeds V_{BAT_PRE} , the GD30WS8662x enters a constant current charge phase. The phase charge current can be programmed via REG01H bit[13:8].

Phase 3 (constant-voltage charge): When the battery voltage rises to the battery-full voltage(V_{BAT_REG}) set via REG02H bit [15:10], the charge mode changes from CC mode to CV mode, and the charge current starts decreasing.

Assuming that the termination function EN_TERM is set via REG02H bit[4] = 1, the charge cycle is considered to be completed when the charge current (I_{CHG}) reaches the termination current threshold (I_{TERM}). The charge status is immediately updated to charge done.

The termination charge current threshold (I_{TERM}) can be programmed via REG01H bit[3:0]. If EN_TERM = 0, the termination fuction is disable and all of the above actions are invalid (see Table 5-1).

Table 5-1. Ter	mination Fucnction Selection	n Table
	After Inst Reaches	

EN_TERM	After I _{BAT} Reaches I _{TERM} in CV Mode		
	Operation	Charge status	
0	Keep CV Charge	Charge	
1	Charge done	Charge done	

Notes:

1. Type: x = Don't Care.

During the entire charging process, the actual charge current may be less than the register setting due to other loop regulations, such as dynamic power management (DPM) regulation (input voltage, input current) or thermal regulation.

A new charge cycle starts when any of the following conditions are valid:

- The input power is recycled.
- Battery charging is enabled via the I²C.
- Auto-recharge kick in.

Under the following conditions:

- No termistor fault at NTC.
- No safety timer fault.
- No battery over-voltage event.
- BATFET is not forced off.





The charger input has back to back blocking FETs to prevent reverse current flow from BAT to BUS. They also integrate control circuitry regulating the input current and prevents excessive currents from being drawn from the input power supply for more reliable operation.

5.4 Auto recharge

When the battery is fully charged and charging is terminated, the battery may be discharged due to system consumption or self-discharge. When the battery voltage is discharge below the recharge threshold and V_{BUS} is still in the operating range, the GD30WS8662x begins another new charging cycle automatically without having to restart a charging cycle manually. The auto-recharge function is valid only when EN_TERM = 1.

5.5 Battery discharge

If the battery is connected and the input source is missing, the BATFET is fully on when V_{BAT} is above the V_{BAT_UVLO} threshold. The 100m Ω BATFET minimizes conduction loss during discharge. The quiescent current of the GDWS8662x is as low as 6.5uA in this mode. The low R_{DS_ON} and low I_Q help extend the running time of the battery.

5.6 Power path management and battery supplyment

The GD30WS8662x employs a pass-through power path structure with the BATFET to decouple the system from the battery. This allows for separate control between the system and the battery. The system is given the priority to start up, even with a deeply discharged or missing battery. When the input power is available, even with a depleted battery, the system voltage is always regulated to V_{SYS_REG} by the integrated LDOFET. The direct power structure consists of a frontend LDOFET between BUS and SYS and a BATFET between SYS and BAT. The LDOFET and BATFET can be controlled by the I²C (see Table 5-2).

Table 5-2. FET Control Via I²C

FET ON/OFF	Hi-Z Mode and Charge Control		
Changed by control	Set EN_HIZ to 1	Set CEB to 0	
LDOFET	ON	х	
BATFET	, v	ON	
(Charging)	x		
BATFET	×	×	
(discharging)	*	x	

Notes:

1. Type: x = Don't Care.

For the system voltage control, when the input voltage is higher than V_{SYS_REG} , the system voltage is regulated to V_{SYS_REG} . When the input voltage is lower than V_{SYS_REG} , the LDOFET is fully on with input current limit. V_{SYS_REG} can be programmed through REG03H bit[3:0].

The charge current is reduced to keep the input current or input voltage in regulation when DPM occurs. If the charge current is reduced to zero and the input source is still overloaded due to a heavy system load, the system voltage begins decreasing. Once the system voltage drops to 30mV below the battery voltage, the GD30WS8662x enters battery supplement mode, and the ideal diode mode is enabled. The BATFET is regulated to keep $V_{BAT} - V_{SYS}$ at 23mV when I_{DSG} (supplement current) * R_{ON_BATFET} is lower than 23mV. In the case that I_{DSG} * R_{ON_BATFET} is higher than 23mV, the BATFET is fully turned on to maintain the ideal forward voltage. When the system load decreases, once V_{SYS} is higher than $V_{BAT} + 23mV$, the ideal diode mode is disabled. Figure 5-4 Dynamic Power Management and Battery Supplement Operation Profile.

When V_{BUS} is not available, the GD30WS8662x operates in discharge mode, and the BATFET is always fully on to reduce loss.



Figure 5-4 Dynamic Power Management and Battery Supplement Operation Profile



5.7 Internal control power supply (LDO)

The integrated LDO not only provides the supply voltage for the IC and also is capable of supplying output up to 50mA current through VCC.

5.8 Interrupt to host (INT)

The GD30WS8662x also has an alert mechanism that can output an interrupt signal via INT to notify the system of the operation by outputting a 256us low-state INT pluse. All of the below events can trigger an INT output.

- Good input source detected (PG_STAT)
- Charge completed
- Charging status change
- Fault in REG04H (watchdog timer fault, thermal fault, safety timer fault, battery OVP fault, NTC fault)

When fault occurs, the GD30WS8662x sends out an INT pulse and latches the fault state in REG04H. After the GD30WS8662x exits the fault state, the fault bit is reset to 0 after the host reads REG04H. The NTC fault bit is not latched and always reports the current thermistor conditions.

The INT signal can be masked when the corresponding control bit is set in REG03H bit[12:8]. When an INT condition is masked, this means that the INT pin signal (and register bit) will not trigged when the corresponding condition occurs. Masking INTs is useful when writing software code to avoid unnecessary interruptions due to these events.



5.9 NTC battery temperature

NTC allows the GD30WS8662x to sense the battery temperature using the thermistor (usually available in the battery pack) to ensure a safe operating environment for the battery. Connect appropriately valued resistors from VCC to NTC to ground. The resistor divider works with a thermistor connected from NTC to ground. The NTC voltage is determined by the resistor divider whose divide ratio depends on the temperature. The GD30WS8662x sets a pre-determined upper and lower bound of the divide ratio for NTC cold and NTC hot internally.

In the GD30WS8662x, the I^2C default setting is PCB_OTP. This function can be changed through the I^2C (see Table 5-3).

	² C Control	Function	
EN_NTC	EN_PCB_OTP	Function	
0 x		Disable	
1	1	NTC	
1	0	PCB_OTP	

Table 5-3. NTC Function Selection Table

Notes:

1. Type: x = Don't Care.

When PCB_OTP is selected and the NTC voltage is lower than the NTC hot threshold, both the LDOFET(Q1) and BATFET are off. The PCB_OTP fault also sets the NTC_FAULT status (REG04H bit[1]) to 1 to show the fault. Operation resumes once the NTC voltage is higher than the NTC hot threshold.

The NTC function works only in charge mode. Once the NTC voltage falls out of this divide ratio, the temperature is outside of the safe operating range, and the GD30WS8662x stops charging and report it on the status bits. Charging resumes automatically after the temperature falls back into the safe range.

5.10 System protection

5.10.1 Input OVP and UVLO protection

The GD30WS8662x has an input over-voltage protection (OVP) threshold and input UVLO threshold. Once the input voltage is out of its normal range, the LDOFET is turned off immediately.

When the input voltage is identified as a good source, a immunity timer becomes active. If the input power is normal until the immunity timer expires, the system start up. Otherwise, Q1 remains off (see Figure 5-5).



Figure 5-5 Input Power Detection Operation Profile



5.10.2 Battery OVP protection

The GD30WS8662x is designed with a built-in battery over-voltage limit (about 130mV higher than V_{BAT_REG}). When a battery over-voltage event occurs, the GD30WS8662x suspends charging immediately and asserts a fault.

5.10.3 Over-discharge current protection

The GD30WS8662x has an over-discharge current protection in discharge mode and supplement mode. Once IDSG exceeds the programmable discharge current limit (2A default), the BATFET turns off after a 60µs delay. The GD30WS8662x enters hiccup mode as part of the over-current protection (OCP). The discharge current limit can be programmed high to 3.2A through the I²C. If the discharge current goes high and reaches the internal fixed current limit (about 3.7A), the BATFET turns off and begins hiccup mode immediately. Similarly, when the battery voltage falls below the programmable V_{BAT_UVLO} threshold (2.76V default), the BATFET turns off to prevent an over-discharge.

5.10.4 Short-circuit protection

The GD30WS8662x features SYS node short-circuit protection (SCP) for both the BUS to SYS path and the BAT to SYS path.

The system voltage is monitored continuously. If V_{SYS} is lower than 1.5V, system SCP for both the BUS to SYS path and the BAT to SYS path is active. I_{DSG} decreases to half of the original value.

For the BUS to SYS path, once I_{BUS} is over the protection threshold, both the LDOFET and BATFET are turned off immediately, and the GD30WS8662x enters hiccup mode. Otherwise, the maximum current limit is not reached. When V_{SYS} is lower than 1.5V and the setting input current limit is reached, the hiccup mode also starts after a 60µs delay. The hiccup mode interval is 800µs.

For the BAT to SYS path, once IBAT is over the 3.7A protection threshold, both the LDOFET and BATFET are turned off immediately, and the GD30WS8662x enters hiccup mode. When



the battery discharge current limit threshold is reached, hiccup mode starts after a 60µs delay. The hiccup mode interval is 800µs.

Particularly, if a system short-circuit occurs when both the input and battery are present, the protection mechanism of both paths works. The faster one of the two dominates the hiccup operation.

For details, please refer to the flow chart shown in Figure 5-6.





5.10.5 Over temperature protection

The GD30WS8662x monitors the internal junction temperature continuously to maximize power delivery and avoid overheating the chip. When the internal junction temperature reaches the preset limit of $T_{J_{REG}}$ (120°C default), the IC starts to reduce the charge current to prevent higher power dissipation. The multiple thermal regulation thresholds from



60~120°C help the system design meet the thermal requirements in different applications. The junction temperature regulation threshold can be set via REG03H bit[5:4]. When the junction temperature reaches 150°C, both Q1 and Q2 turn off.

5.10.6 Safety timer

The GD30WS8662x provides both a pre-charge and constant current charge safety timer to prevent an extended charging cycle due to abnormal battery conditions. The safety timer is 1hr when the battery voltage is lower than V_{BAT_PRE} . The constant current(CC) charge safety timer starts when the battery enters CC charge mode. The CC charge safety timer can be programmed through the l²C. The safety timer can be disabled via the l²C.

The following actions can restart the safety timer.

- A new charge cycle is kicked in.
- Write REG00H bit[3] from 1 to 0 (charge disable to enable).
- Write REG00H bit[4] from 1 to 0 (HIZ enable to disable).

5.11 Host mode and default mode

The GD30WS8662x is a host-controlled device. After the power-on reset, the GD30WS8662x starts up in a watchdog timer expiration state or default mode. All registers are in their default settings.

The watchdog timer works in both charge and discharge mode. When the watchdog timer run out, most registers return to the default value (refer to the l²C Register Map section on 5.14). When the watchdog timer is out in both charge and discharge mode, both the LDOFET and BATFET are turned off. They turn on again automatically after t_{RST_DUR} , which can be programmed by REG00H bit[5].

To save quiescent current during discharge mode, the watchdog timer can be turned off during by setting REG02H bit[7] to 0.

Any write to the GD30WS8662x switches it to host mode. All charge parameters are programmable. If the watchdog timer (REG02H bit[6:5]) is not disabled, the host must reset the watchdog timer regularly by writing 1 to REG01H bit[14] before the watchdog timer expires to keep the device in host mode. Once the watchdog timer expires, the GD30WS8662x goes back to default mode. The watchdog timer limit can also be programmed or disabled by the host control.





Figure 5-7 Host Mode and Default Mode Selection

Notes:

1. Once the watchdog timer expires, the I²C watchdog timer must be reset or will not be valid in the next cycle.



5.12 Shipping mode

In applications where the battery is not removable, it is essential to disconnect the battery from the system for shipping mode or to allow the system power to be reset during the application. The GD30WS8662x provides both shipping mode (shown in Table 5-4) and system reset mode for different applications.

Table	5-4.	Shipping	Mode	Control
	• ••	•ppg		

Items	Enter Shipping Mode	Exit Shipping Mode			
nems	Set FET_DIS to 1	INT H to L for 2s	VBUS Plug-In		
LDOFET	х	х	On		
BATFET(Charging)	Off(t _{SMEN_DGL} later)	On	On(2s later)		
BATFET(Discharging)	Off(tsmen_dgl later)	On	On(2s later)		

Notes:

1. Type: x = Don't Care.

The GD30WS8662x has a register bit for battery disconnection control (FET_DIS). If this bit is set to 1, the GD30WS8662x enters shipping mode after a delay time, which can be programmed by REG04H bit[7:6]. The BATFET turns off, and the FET_DIS bit refreshes to 0 after the BATFET turns off. Pull the INT pin down or plug in the input adapter for 2s to wake the GD30WS8662x up from shipping mode.

The GD30WS8662x can also reuse an INT pin to cut off the path from the battery to the system under the condition needed to reset the system manually. Once the logic at INT is set low for longer than t_{RST_DGL} (which can be programmed by REG00H bit[7:6]), the battery is disconnected from the system by turning off the BATFET. The off state lasts for t_{RST_DUR} , which can be programmed by REG00H bit[5]. Then the BATFET is turned on automatically, and the system is powered by the battery again. During the off period, the INT pin is not limited to be high or low.

When the IC exits shipping mode, only registers that can be reset by the watchdog can be reset.

The GD30WS8662x can reset the system by controlling the INT pin(see Figure 5-8).



Figure 5-8 System Reset Function Operation Profile

5.13 I²C interface

The I²C (inter-integrated circuit) module provides an I²C interface which is an industry standard two-line serial interface for MCU to communicate with external I²C interface. I²C bus uses two serial lines: a serial data line (SDA), and a serial clock line (SCL).

The I²C interface implements standard I2C protocol with standard-mode (up to 100 kHz) and fast-mode (up to 400 kHz). The I²C interface only supports Slave-mode. The I²C interface receive data on rising SCL and transmit data on falling SCL.





8bit function (2'b10 + 5bit(register address), +1bit(1'b0-write, 1'b1-read))

- + 8bit data[15:8]
- + 8bit data[7:0].



5.14 Register map

Table 5-5. GD30WS866x Register Map

Register Name	Address	R/W	Description	Default
REG00H	0,400	*/	Input course control and Dower on configuration register	10011111
REGUUN	0x00	r/w	Input source control and Power on configuration register	10101100
DEODALL	004	-	Charge current control register and Discharge/termination	00001111
REG01H 0x01 r/w			current	10010001
			Charge voltage control and Charge termination/timer	10100011
REG02H	0x02	r/w	control register	00111010
DECOOL	000	r/w	Miscellaneous operation control and System voltage	11000000
REG03H	REG03H 0x03 r/		regulation register	00111001
	0.404	-	Queters status and Equilt register	00100000
REG04H	0x04	r/w	System status and Fault register	0000000

5.14.1 REG00H

Address: 0b 00000

Bits	Name	POR	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	VBUS_MIN [3]	1	Y	Ν	r/w	640mV	
14	VBUS_MIN [2]	0	Y	Ν	r/w	320mV	Offset: 3.88V Range: 3.88V - 5.08V
13	VBUS_MIN [1]	0	Y	Ν	r/w	160mV	Default: 4.60V (1001)
12	VBUS_MIN [0]	1	Y	Ν	r/w	80mV	
11	IBUS_LIM [3]	1	Y	Ν	r/w	240mA	
10	IBUS_LIM [2]	1	Y	Ν	r/w	120mA	Offset: 50mA Range: 50mA - 500mA
9	IBUS_LIM [1]	1	Y	Ν	r/w	60mA	Default: 500mA (1111)
8	IBUS_LIM [0]	1	Y	Ν	r/w	30mA	
7	tRST_DGL[1]	1	Y	Ν	r/w	00: 8s 01: 12s	Pull INT low to disconnect the battery.
6	tRST_DGL [0]	0	Y	Ν	r/w	10: 16s 11: 20s	Default: 16s (10)
5	tRST_DUR	1	Y	Y	r/w	0: 2s 1: 4s	Battery FET is off for a period of time before auto- on Default: 4s (1)
4	EN_HIZ1	0	Y	Y	r/w	0: Disable 1: Enable	Default: Disable (0)
3	СЕВ	1	Y	Υ	r/w	0: Charge enable 1: Charge disabled	Charge configuration Default: charge disabled (1)
2	VBAT_UVLO [2]	1	Y	Y	r/w	440mV	Battery UVLO threshold Offset: 2.6V Range: 2.6V - 3.37V



Bi	ts	Name	POR	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
1		AT_UVLO	0	Y	Y	r/w	220mV	Default: 3.04V (100)
() [0]	AT_UVLO	0	Y	Y	r/w	110mV	

Notes:

1. This bit only controls the on and off function of the LDOFET(Q1).

5.14.2 REG01H

Address:	0b 00001

Bits	Name	POR	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	Register Reset	0	Y	Ν	r/w	0: Keep current setting 1: Reset	Default: Keep current register setting (0)
14	I2C Watchdog Timer Reset	0	Y	Ν	r/\	0: Normal 1: Reset	Default: Normal (0)
13	ICC [5]	0	Y	Y	r/w	256mA	
12	ICC [4]	0	Y	Y	r/w	128mA	Constant charge current
11	ICC [3]	1	Y	Y	r/w	64mA	setting.
10	ICC [2]	1	Y	Y	r/w	32mA	Offset: 8mA Range: 8mA (000000) -
9	ICC [1]	1	Y	Y	r/w	16mA	456mA (111000)
8	ICC [0]	1	Y	Y	r/w	8mA	Default: 128mA (001111)
7	IDSG[3]	1	Y	Y	r/w	1600mA	BAT to SYS discharge current limit.
6	IDSG[2]	0	Y	Y	r/w	800mA	Offset: 200mA
5	IDSG[1]	0	Y	Y	r/w	400mA	Range: 400mA - 3.2A
4	IDSG[0]	1	Y	Y	r/w	200mA	Valid range: 0001 - 1111 Default: 2000mA (1001)
3	ITERM [3]	0	Y	Y	r/w	16mA	Termination current.
2	ITERM [2]	0	Y	Y	r/w	8mA	Offset: 1mA
1	ITERM [1]	0	Y	Y	r/w	4mA	Range: 1mA - 31mA
0	ITERM [0]	1	Y	Y	r/w	2mA	Default: 3mA (0001)

5.14.3 REG02H

Address: 0b 00002



Bits	Name	POR	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	VBAT_REG [5]	1	Y	Y	r/w	480mV	
14	VBAT_REG [4]	0	Y	Y	r/w	240mV	Battery regulation voltage.
13	VBAT_REG [3]	1	Y	Y	r/w	120mV	Offset: 3.60V
12	VBAT_REG [2]	0	Y	Y	r/w	60mV	Range: 3.60V - 4.545V
11	VBAT_REG [1]	0	Y	Y	r/w	30mV	Default: 4.2V (101000)
10	VBAT_REG [0]	0	Y	Y	r/w	15mV	
9	VBAT_PRE	1	Y	Y		0: 2.8V	Pre-charge to constant charge threshold. Default: 3.0V (1)
8	VRECH	1	Y	Y		0: 100mV 1: 200mV	Battery recharge threshold (below V _{BAT_REG}). Default: 200mV (1)
7	EN_WD_ DISCHG	0	Y	Ν		0: Disable	Watchdog control in discharge mode. Default: Disable (0)
6	WATCHDOG [1]	0	Y	Ν		$01 \cdot 40c$	I2C watchdog timer limit. Default: 40s (01)
5	WATCHDOG [0]	1	Y	Ν		10: 80s 11: 160s	If Bit[6:5] = 00, then watchdog timer is disabled regardless of whether bit[7] is set or not.
4	EN_TERM	1	Y	Y	-	0: Disable 1: Enable	Termination setting (controlling the termination is allowed or not). Default: Enable (1)
3	EN_TIMER	1	Y	Y	r/w	0: Disable 1: Enable	Safety timer setting. Default: Enable timer (1)
2	CHG_TMR [1]	0	Y	Y	r/\\/	00: 3hrs 01: 5hrs	Constant charge timer.
1	CHG_TMR [0]	1	Y	Y	rha	10.01	Default: 5hrs (01)
0	RSVD	RSVD	RSVD	RSVD		-	RSVD

5.14.4 REG03H

Bits	Name	POR	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	EN_NTC	1	Y	Y	r/\w	0: Disable 1: Enable	Default: Enable (1)
14	TMR2X_EN	1	Y	Y	r/w	0: Disable 2X extended safety timer during PPM 1: Enable 2X extended safety timer during PPM	Delault. Ellable (1)
13	FET_DIS (2)	0	Y	Ν	r/\\/	0: Enable 1: Turn off	Default: Enable (0)
12	PG_INT_	0	Y	Y	r/w	0: On	Default: On (0)



Bits	Name	POR	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
	Control					1: Off	
11	EOC_INT_ Control	0	Y	Y	rlad	0: On 1: Off	Charge completed INT mask control Default: On (0)
10	CHG STATUS_INT_ Control	0	Y	Y	r/w	0: On 1: Off	Charging status change INT mask control (charging status contain: not charging, pre charge and charge). Default: On (0)
9	NTC_INT_ Control	0	Y	Y	r/\	0: On 1: Off	Default: On (0)
8	BATOVP_INT_ Control	0	Y	Y	r/\\/	0: On 1: Off	Default: On (0)
7	EN_PCB_OTP	0	Y	Y	r/\	0: Enable 1: Disable	PCB_OTP enable. Default: Enable (0)
6	EN_VBUSLOO P	0	Y	Y	r/\\/	0: Enable 1: Disable	Default: Enable (0)
5	TJ_REG [1]	1	Y	Y		00: 60°C	Thermal regulation
4	TJ_REG [0]	1	Y	Y	-	01: 80°C 10: 100°C 11: 120°C	threshold. Default: 120°C (11)
3	VSYS_REG [3]	1	Y	Y	r/w	400mV	
2	VSYS_REG [2]	0	Y	Y	r/w	200mV	System voltage regulation. Offset: 4.2V
1	VSYS_REG [1]	0	Y	Y	r/w	100mV	Range: 4.2V Default: 4.65V (1001)
0	VSYS_REG [0]	1	Y	Y	r/w	50mV	

5.14.5 REG04H

Address: 0b 00100

Bits	Name	POR	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
15	WATCHDOG_ FAULT	0	Y	N/A	r	0: Normal 1: Watchdog timer expiration	Normal (0)
14	Rev [1]	0	N/A	N/A	r	01.00300030002X	Revision number.
13	Rev [0]	1	N/A	N/A	r	10: reserved 11: reserved	Default: (01)
12	CHG_STAT [1]	0	N/A	N/A		00: Not charging 01: Pre charge	Natabarring (00)
11	CHG_STAT [0]	0	N/A	N/A	-	10: Charge 11: Charge done	Not charging (00)



Bits	Name	POR	Reset by REG_RST	Reset by WTD	R/W	Description	Comment
10	PPM_STAT	0	N/A	N/A	r .	0: No PPM 1: In PPM	No PPM (0)
9	PG_STAT	0	N/A	N/A	r	1. Power good	No power good (0)
8	THERM_STAT	0	N/A	N/A	r	0: No thermal regulation 1: In thermal regulation	Normal (0)
7	en_shipping _dgl[1]	0	Y	Ν		00: 1s 01: 2s	Enter shipping mode
6	EN_SHIPPING _DGL[0]	0	Y	Ν		10: 4s 11: 8s	deglitch time Default: 1s (00)
5	VBUS_FAULT	0	N/A	N/A	r	0: Normal 1: VBUS fault (OVP or bad source)	Normal (0)
4	THEM_SD	0	N/A	N/A		0: Normal 1: Thermal shutdown	Normal (0)
3	BAT_FAULT	0	N/A	N/A	r	0: Normal 1: Battery OVP	Normal (0)
2	STMR_FAULT	0	N/A	N/A	r	0: Normal 1: Safety timer expiration	Normal (0)
1	NTC_FAULT [1]	0	N/A	N/A	r	0: Normal 1: NTC hot	Normal (0)
0	NTC_FAULT [0]	0	N/A	N/A		0: Normal 1: NTC cold	Normal (0)



6 Electrical characteristics

6.1 Absolute maximum ratings

The maximum ratings are the limits to which the device can be subjected without permanently damaging the device. Note that the device is not guaranteed to operate properly at the maximum ratings. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

Symbol	Parameter	Min	Max	Unit
V _{BUS}	Power supply pin from BUS other 5V input	-0.3	7	V
V _{BUS}	Power supply pin from BUS other 5V input, pulsed less than 20us		32	V
V _{BAT}	Battery voltage	-0.3	7	V
V _{SYS}	System Voltage	-0.3	7	V
V _{cc}	LDO output voltage and Internal logic voltage (VCC, NTC, INT,	-0.3	7	V
	SCL, SDA)			
TJ	Operating junction temperature,	-40	150	°C
T _{stg}	Storage temperature,	-65	150	°C

Table 6-1 Absolute Maximum Ratings

6.2 Recommended operation conditions

Symbol	Parameter	Min	Max	Unit
V _{BUS}	Power supply pin from BUS other 5V input	4.35	5.5	V
V _{BAT}	Battery voltage		4.65	V
V _{SYS}	System Voltage		5	V
V _{cc}	LDO output voltage and Internal logic voltage (VCC, NTC, INT,	3.15	_	V
	SCL, SDA)			
TJ	Operating Junction temperature	-40	+125	°C

Table 6-2 Recommended Operation Conditions

Notes:

1. When the GD30WS8662x is in shipping mode, the maximum VCC is $max(V_{BUS}, V_{BAT})$, and the maximum VCC is 3.45V in other modes.

6.3 Electrical sensitivity

The device is strained in order to determine its performance in terms of electrical sensitivity. Electrostatic discharges (ESD) are applied directly to the pins of the sample. Static latch-up (LU) test is based on the two measurement methods.



Table 6-3 Electrostation	Discharge and Latch-up
--------------------------	------------------------

Symbol	Parameter	Conditions	Value	Unit				
Vesd(hbm)	human body model	T _A = 25 °C;	. 2000	V				
		JS-001-2017	±2000	v				
Vesd(CDM)	charge device model	T _A = 25 °C;	. 1000	Ň				
		JS-002-2018	±1000	V				
Latab un	l-test	T _A = 25 °C;	. 200					
Latch up		JESD78E	±200	mA				

6.4 Power supplies voltage and current

All parameters are tested at $T_A = -40^{\circ}$ C to +125°C, $V_{BUS} = 5$ V or $V_{BAT} = 5$ V (unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		VBUS = 5V, CEB = 0, ISYS = 0A,		15		uA
		charge done, VBAT = 4.35V	_	15		uA
		VBUS = GND, CEB = 1, ISYS = 0A,				
		VBAT = 4.35V, disable PCB_OTP		6.5	8.5	μA
IBAT_Q	Battery quiescent current	function, not including the current	_	0.5		μΑ
		from the external NTC resistor				
		VBUS = GND, CEB = 1, ISYS = 0A,		14.5	22	
		VBAT = 4.35V, enable PCB_OTP				uA
		function, not including the current	_	14.5	22	uA
		from the external NTC resistor				
Ishipping	Current in shipping mode	VBAT = 4.5V, VBUS = VSYS = GND,),		200	nA
		FET_DIS = 1, shipping mode	_		200	ΠA
V _{CC}	VCC regulator voltage	$I_{Vcc} = 0$ to 50 mA	3.15	3.3	3.45	V

Table 6-4 Power Supplies Voltages and Currents

6.5 Logic input characteristics

All parameters are tested at $T_A = -40^{\circ}$ C to $+125^{\circ}$ C, $V_{BUS} = 4.5$ to 5.5 V (unless otherwise noted)

Table 6-5	Logic	Input	Characteristics
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL}	Input logic low voltage	_	0		0.8	V
V _{IH}	Input logic high voltage	—	1.5	_	5.5	V
V _{HYS}	Input logic hysteresis	—	100	_	—	mV

6.6 Open drain outputs characteristics

Open drain output pins include INT, SDA.

All parameters are tested at $T_A = -40^{\circ}$ C to $+125^{\circ}$ C, $V_{BUS} = 4.5$ to 5.5 V (unless otherwise noted)



Table 6-6 Open Drair	Output Characteristics
----------------------	------------------------

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{INT}	Output logic low voltage	lo = 5 mA	_	_	0.1	V
V_{SDA}	Output logic low voltage	lo = 5 mA	_	_	0.1	V
I _{OD}	Output high impedance	$V_{O} = 5 V$	-2	_	2	μA
	leakage					

6.7 Input source and battery protection

All parameters are tested at V_{BUS} = 5.0V, V_{BAT} = 3.5V, T_A = +25 $^{\circ}\,$ C (unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	VBUS under-voltage	VDLIC folling	2.62	3.73	2.02	v
	lockout threshold	VBUS falling	3.62	3.13	3.82	v
V _{BUS_UVLO}	VBUS under-voltage					
	lockout threshold	VBUS rising	—	170		mV
	hysteresis					
	VBUS over-voltage	VPLIS rising throshold	5.85	6	6.15	V
	protection threshold	VBUS rising threshold	5.65	0	0.15	v
VBUS_OVP	VBUS over-voltage	_				
	protection threshold		—	340	-	mV
	hysteresis					
Vhdrm	VBUS vs. battery					
	voltage headroom	VBUS rising vs. battery	80	130	170	mV
	threshold					
	VBUS vs. battery					
	voltage headroom	_	—	65	—	mV
	threshold hysteresis					
		VBAT voltage rising,	2.5	2.6	2.7	V
	Battery under-	REG01[2:0] =000	2.5	2.0	2.1	v
	voltage lockout	VBAT voltage rising,	2.94	3.04	3.14	V
	threshold	REG01[2:0] =100	2.94	3.04	3.14	v
VBAT_UVLO	theshold	VBAT voltage rising,	3.27	3.37	3.47	v
		REG01[2:0] =111	5.27	3.37	3.47	v
	Battery under-					
	voltage threshold	VBAT_UVLO = 2.46V	—	140	—	mV
	hysteresis					
	Battery over-voltage	Rising, higher than VBAT_REG	_	130		mV
VDAT OVD	protection threshold			130		111V
VBAT_OVP	Battery over-voltage	_		65		mV
	protection hysteresis	_		00		IIIV

Table 6-7 Input Source and Battery Protection



6.8 Power path management

All parameters are tested at V_{BUS} = 5.0V, V_{BAT} = 3.5V, T_A = +25 $^{\circ}$ C (unless otherwise noted)

Table 6-8 Power Path Management

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		VBUS = 5.5V, RSYS = 100Ω,				
		ICHG = 0A,			•	%
		REG03[3:0] = 0000,	-2		2	
		VSYS_REG = 4.2V				
	Regulated system	VBUS = 5.5V, RSYS = 100Ω,				
	c ,	ICHG = 0A,	-2		2	%
Vsys_reg_acc	output voltage	REG03[3:0] = 1001,	-2		Z	70
	accuracy	VSYS_REG = 4.65V				
		VBUS = 5.5V, RSYS = 100Ω,				
		ICHG = 0A,	2		2	%
		REG03[3:0] = 1111,	-2		2	70
		VSYS_REG = 4.95V				
		REG00[11:8] = 0000,	40	50	60	
	VBUS current limit	IBUS_LIM = 50mA	40	50	00	mA
		REG00[11:8] = 0011,	125	140	155	
		IBUS_LIM = 140mA	125	140	100	
BUS_LIM		REG00[11:8] = 1001,	295	320	345	ШA
		IBUS_LIM = 320mA		320	545	
		REG00[11:8] = 1111,	455	500	545	
		IBUS_LIM = 500mA		500	545	
		REG00[15:12] = 0000,		2 00	4 4 0	
	VBUS minimum	VBUS_MIN = 3.88V		3.88	4.18	V
Mana		REG00[15:12] = 1001,		4 60	475	
V _{BUS_MIN}	voltage regulation	VBUS_MIN = 4.60V		4.60	4.75	v
		REG00[15:12] = 1111,	4.88	F 00	5.35	
		VBUS_MIN = 5.08V	4.00	5.08	5.55	
R _{ON_Q1}	BUS to SYS switch	VBUS = 4.5V, ISYS = 100mA		290		mΩ
INON_Q1	on resistance	VB03 = 4.3V, 1313 = 100IIIA		230		11152
		VBUS = 5.5V, EN_HIZ = 0, CEB = 0,				
	VBUS quiescent	charge enable, ICHG = 0A,	—	2.1	—	
Ibus_q	current	ISYS = 0A				mA
	Current	VBUS = 5.5V, EN_HIZ = 0, CEB = 1,		1.0		1
		charge disabled		— 1.9		
		VBUS = 5V, CEB = 0, ISYS = 0A,		15		
IBAT_Q	Battery quiescent	charge done, VBAT = 4.35V		15		
IDAI_Q	current	VBUS = GND, CEB = 1, ISYS = 0A,		6.5	8.5	uA
		VBAT = 4.35V, disable PCB_OTP		0.5	0.5	



		function, not including the current				
		from the external NTC resistor				
		VBUS = GND, CEB = 1, ISYS = 0A,				
		VBAT = 4.35V, enable PCB_OTP		14.5	22	
		function, not including the current	_	14.0	22	
		from the external NTC resistor				
		VBAT = 4.5V, VBUS = VSYS = GND,			200	nA
		FET_DIS = 1, shipping mode			200	ПА
David	B-FET on resistance	VBUS < 2V, VBAT = 3.5V,		100	_	2
Ron_q2		ISYS = 100mA	_			mΩ
1	B-FET discharge	REG01[7:4] = 0001, IDSG = 400mA	_	400	_	mA
IDSG	current limit	REG01[7:4] = 1001, IDSG = 2000mA	_	2000	_	mA
	Ideal diode forward					
VFWD	voltage in	50mA discharge current	—	23	_	mV
	supplement mode					

6.9 Shipping mode

All parameters are tested at V_{BUS} = 5.0V, V_{BAT} = 3.5V, T_A = +25 $^{\circ}$ C (unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
toursu pou	Enter shipping mode	REG03[13] is set from 0 to 1,		1		6
tsmen_dgl	deglitch time	REG04[7:6] = 00		I	_	S
+	Exit shipping mode by			2		0
tsmex_dgl	INT is pulled low		2		S	

6.10 Auto-reset mode

All parameters are tested at V_{BUS} = 5.0V, V_{BAT} = 3.5V, T_A = +25 $^{\circ}$ C (unless otherwise noted)

Table 6-10 Auto-Reset Mode

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	Reset by INT	REG00H[7:6] = 00		8	—	
t _{RST_DGL}	—	REG00H[7:6] = 10	_	16	_	S
trst_dur	BFET off lasting time	REG00H[5] = 0	_	2	_	
	—	REG00H[5] = 1	_	4	_	S

6.11 Battery charger

All parameters are tested at VBUS = 5.0V, VBAT = 3.5V, TA = +25 $^{\circ}$ C (unless otherwise noted)



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		REG02[15:10] = 000000,	2 5 0 0	2.0	3.618	
		$V_{BAT_REG} = 3.6V$	3.582	3.6	3.018	
		REG02[15:10] = 101000,	4.188	4.2	4.212	
\/	Battery charge voltage	$V_{BAT_{REG}} = 4.2V$	4.100	4.2	4.212	V
Vbat_reg	regulation	REG02[15:10] = 110010,	4.358	4.38	4.44	v
		$V_{BAT_REG} = 4.38V$	4.500	4.30	4.44	
		REG02[15:10]= 111110,	4.522	4.53	4.568	
		$V_{BAT_REG} = 4.53V$	4.522	4.55	4.500	
lcc	Constant current	REG01[13:8] = 001111, Icc = 128mA	113	128	137	mA
ICC		REG01[13:8] = 111000, I _{CC} = 456mA	424	456	488	ШA
T_{J_REG}	Junction temperature regulation ⁽¹⁾	Thermal_Limit = 120°C	_	120	_	°C
l	Dro oborgo ourront			20%		
IPRE	Pre-charge current			*lcc		
		REG01[3:0] = 0000, I _{TERM} = 1mA		0.95	_	
I	Charge termination	REG01[3:0] = 0001, I _{TERM} = 3mA		3.05	_	A
Iterm	current threshold	REG01[3:0] = 0101, I _{TERM} = 11mA	_	11	—	mA
		REG01[3:0] = 0101, I _{TERM} = 31mA		31	—	
V	Pre-charge to constant current charge threshold	V _{BAT} rising, REG02[9] = 1, V _{BAT_PRE} = 3.0V	2.9	3	3.1	V
Vbat_pre	Pre-charge to constant					
	current charge	—	—	320	—	mV
	threshold hysteresis					
Vacau	Battery auto-recharge	Below VBAT_REG, REG02[8] = 0	55	100	145	mV
V _{RECH}	voltage threshold	Below VBAT_REG, REG02[8] = 1	155	200	245	IIIV

Table 6-11 Battery Charger

6.12 Thermal protection

All parameters are tested at VBUS = 5.0V, VBAT = 3.5V, TA = +25 $^{\circ}$ C (unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
	Thermal shutdown			450		°C	
T. SURV	threshold ⁽¹⁾		_	150	_	¹	
TJ_SHDN	Thermal shutdown			20		°C	
	hysteresis (1)	—		20	_		
INTC	NTC output current	CEB = 0, NTC = 3V	-1	0	1	uA	
	NTC cold temp rising		63	05	07	0/	
VCOLD	threshold	As a percentage of VCC		65	67	%	
	NTC cold temp rising	_	—	60	_	mV	

Table 6-12 Thermal Protection



	threshold hysteresis					
	NTC hot temp falling	As a parasitors of VCC		33	35	%
VHOT	threshold	As a percentage of VCC	31	55	30	70
VHOI	NTC hot temp falling			70		mV
	threshold hysteresis		_	70		mv
	NTC hot temp falling					
	threshold for	As a percentage of VCC		32	35	%
Vнот_рсв	PCB_OTP					
	NTC hot temp falling					
	threshold hysteresis	—		90	—	mV
	for PCB_OTP					

6.13 Watchdog timer

All parameters are tested at VBUS = 5.0V, VBAT = 3.5V, TA = +25 $^{\circ}$ C (unless otherwise noted)

Table 6-13 Watchdog Timer

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
twdt	Watchdog timer	REG0[6:5] = 11	_	160		s

Notes:

1. Guaranteed by design.



6.14 Typical Characteristics





7

Typical application circuit

Figure 7-1 Typical GD30WS8662x Application Circuit

In this application, the GD30WS8662x is used to single-cell battery charging for wireless wearables.







Layout guideline



Notes:

- 1) Place the bypass capacitors as close to the IC as possible to ensure the smallest input inductance and ground impedance.
- 2) Place the PCB trace connecting the capacitor between VCC and GND very close to the IC.
- 3) Place the l²C wire in parallel.
- 4) Place via in the INT pin and route from the bottom layer.



9 Package information

9.1 WLCSP-9 package outline and dimensions

Figure 9-1 WLCSP-9 Package Outline



Table 9-1 WLCSP-9 Dimensions (in mm)

Symbol	Min	Тур	Max
A	0.55	0.6	0.65
A1	0.295	0.325	0.355
A2	0.23	0.25	0.27
A3	—	0.025	—
b	0.28	0.31	0.34
D	1.73	1.75	1.77
E	1.73	1.75	1.77
e	—	0.707	_
e1	—	0.5	—
e2	—	0.5	_
f	—	0.375	_
X1	—	0.22	_
X2	—	0.22	—
Y1	—	0.22	—
Y2		0.22	

(Original dimensions are in millimeters)



Figure 9-2 WLCSP-9 recommended footprint



(All dimensions are in millimeters)

9.2 Thermal characteristics

Thermal resistance is used to characterize the thermal performance of the package device, which is represented by the Greek letter " Θ ". For semiconductor devices, thermal resistance represents the steady-state temperature rise of the chip junction due to the heat dissipated on the chip surface.

 Θ_{JA} : Thermal resistance, junction-to-ambient.

 Θ_{JB} : Thermal resistance, junction-to-board.

OJC: Thermal resistance, junction-to-case.

 Ψ_{JB} : Thermal characterization parameter, junction-to-board.

 Ψ_{JT} : Thermal characterization parameter, junction-to-top center.

$$\Theta_{JA} = (T_J - T_A)/P_D$$

$$\Theta_{JB} = (T_J - T_B)/P_D$$

 $\Theta_{\rm JC} = (T_{\rm J} - T_{\rm C})/P_{\rm D}$

Where, T_J = Junction temperature.

T_A = Ambient temperature

- T_B = Board temperature
- T_{C} = Case temperature which is monitoring on package surface
- P_D = Total power dissipation

 Θ_{JA} represents the resistance of the heat flows from the heating junction to ambient air. It is an indicator of package heat dissipation capability. Lower Θ_{JA} can be considerate as better overall thermal performance. Θ_{JA} is generally used to estimate junction temperature.



 Θ_{JB} is used to measure the heat flow resistance between the chip surface and the PCB board.

 Θ_{JC} represents the thermal resistance between the chip surface and the package top case. Θ_{JC} is mainly used to estimate the heat dissipation of the system (using heat sink or other heat dissipation methods outside the device package).

Table 9-2 Package Thermal Characteristics⁽¹⁾

Symbol	Condition	Package	Value	Unit
Θја	Natural convection, 2S2P PCB	WLCSP9	69.16	°C/W
Θјв	Cold plate, 2S2P PCB	WLCSP9	15.25	°C/W
ΘJC	Cold plate, 2S2P PCB	WLCSP9	13.16	°C/W
ψ_{JB}	Natural convection, 2S2P PCB	WLCSP9	RSVD	°C/W
Ψ_{JT}	Natural convection, 2S2P PCB	WLCSP9	RSVD	°C/W

(1) Thermal characteristics are based on simulation, and meet JEDEC specification.



10 Ordering information

Table 10-1 Part order code for GD30WS8662X

Part Order Code	Package	Package Type	Temperature Operating Range
GD30WS8662DYTR	WLCSP-9	Green	Industrial -40°C to +125°C



11 Revision history

Table 11-1 Revision history

Revision No.	Description	Date
1.0	Initial	Mar.30, 2022



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